

Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- ► Low C_{ISS} and fast switching speeds
- Excellent thermal stability
- Integral source-drain diode
- ► High input impedance and high gain
- ► Complementary N- and P-Channel devices

Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

General Description

The Supertex 2N7002 is an enhancement-mode (normally-off) transistor that utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

| Device | Package Option | BV _{DSS} /BV _{DGS} (V) | $R_{DS(ON)} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $ | I _{D(ON)} (min) (A) |
|----------|-------------------|--|---|------------------------------------|
| 2N7002-G | TO-236AB (SOT-23) | 60 | 7.5 | 0.5 |





-G indicates package is RoHS compliant ('Green')

Absolute Maximum Ratings

| Parameter | Value |
|-----------------------------------|-------------------|
| Drain-to-source voltage | BV _{DSS} |
| Drain-to-gate voltage | BV _{DGS} |
| Gate-to-source voltage | ±30V |
| Operating and storage temperature | -55°C to +150°C |
| Soldering temperature* | +300°C |

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration



TO-236AB (SOT-23)

Product Marking



W = Code for week sealed
_____ = "Green" Packaging

TO-236AB (SOT-23)

^{*} Distance of 1.6mm from case for 10 seconds.

Thermal Characteristics

| Package | l _D (continuous) [†] (mA) | I _D (pulsed) (mA) | Power Dissipation @T _A = 25°C (W) | θ _{jc} (°C/W) | θ _{ja} (°C/W) | l _{DR} [†] (mA) | I _{DRM} (mA) |
|----------|---|------------------------------------|--|---------------------------|---------------------------|--------------------------------------|--------------------------|
| TO-236AB | 115 | 800 | 0.36 | 200 | 350 | 115 | 800 |

Notes:

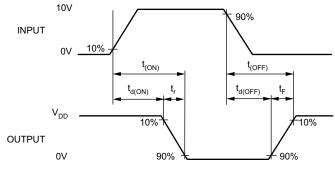
Electrical Characteristics (T_A = 25°C unless otherwise specified)

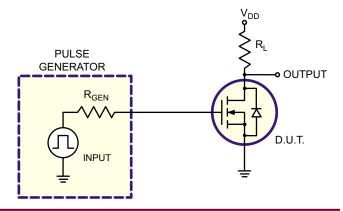
| Sym | Parameter | Min | Тур | Max | Units | Conditions | | |
|-----------------------------|--|-----|-----|------|-------|--|--|--|
| BV _{DSS} | Drain-to-source breakdown voltage | 60 | - | - | V | $V_{GS} = 0V, I_{D} = 10\mu A$ | | |
| $V_{\rm GS(th)}$ | Gate threshold voltage | 1.0 | - | 2.5 | V | $V_{GS} = V_{DS}, I_{D} = 250 \mu A$ | | |
| $\Delta V_{GS(th)}$ | Change in V _{GS(th)} with temperature | - | ı | -5.5 | mV/°C | $V_{GS} = V_{DS}, I_{D} = 250 \mu A$ | | |
| I _{GSS} | Gate body leakage current | - | 1 | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | | |
| | | - | - | 1.0 | | $V_{GS} = 0V, V_{DS} = Max rating$ | | |
| I _{DSS} | Zero gate voltage drain current | - | ı | 500 | μA | $V_{GS} = 0V$, $V_{DS} = 0.8$ Max rating, $T_A = 125$ °C | | |
| I _{D(ON)} | On-state drain current | | 1 | - | mA | V _{GS} = 10V, V _{DS} = 25V | | |
| В | Static drain-to-source | - | ı | 7.5 | Ω | $V_{GS} = 5.0V, I_{D} = 50mA$ | | |
| R _{DS(ON)} | on-state resistance | - | ı | 7.5 | 1 12 | $V_{GS} = 10V, I_{D} = 500mA$ | | |
| $\Delta R_{	extsf{DS(ON)}}$ | Change in R _{DS(ON)} with temperature | - | 1 | 1.0 | %/°C | $V_{GS} = 10V, I_{D} = 500mA$ | | |
| G _{FS} | Forward transconductance | 80 | - | - | mmho | $V_{DS} = 25V, I_{D} = 500mA$ | | |
| C _{ISS} | Input capacitance | - | - | 50 | | $V_{GS} = 0V$, | | |
| C _{oss} | Common source output capacitance | - | - | 25 | pF | $V_{DS} = 25V$ | | |
| C _{RSS} | Reverse transfer capacitance | - | - | 5.0 | | f = 1.0MHz | | |
| t _(ON) | Turn-on time | - | - | 20 | ne | $V_{DD} = 30V$, $I_{D} = 200$ mA, $R_{GEN} = 25\Omega$ | | |
| t _(OFF) | Turn-off time | - | - | 20 | ns | | | |
| V _{SD} | Diode forward voltage drop | - | 1.2 | - | V | V _{GS} = 0V, I _{SD} = 200mA | | |
| t _{rr} | Reverse recovery time | - | 400 | - | ns | V _{GS} = 0V, I _{SD} = 800mA | | |

Notes:

- All D.C. parameters 100% tested at 25° C unless otherwise stated. (Pulse test: 300μ s pulse, 2% duty cycle.) All A.C. parameters sample tested.

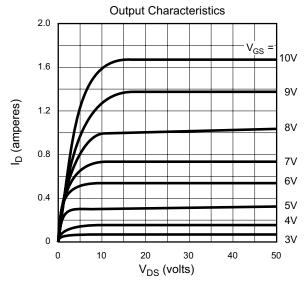
Switching Waveforms and Test Circuit

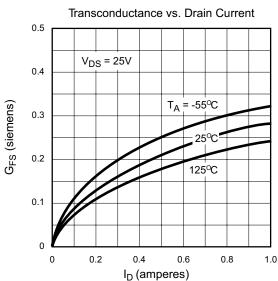


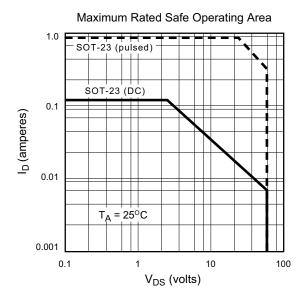


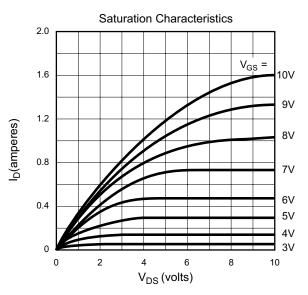
[†] I_D (continuous) is limited by max rated T_C

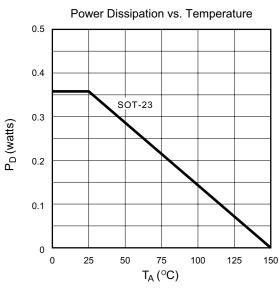
Typical Performance Curves

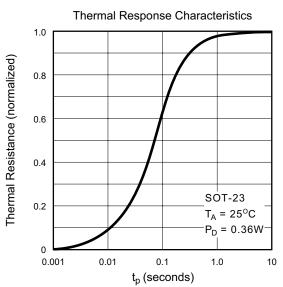




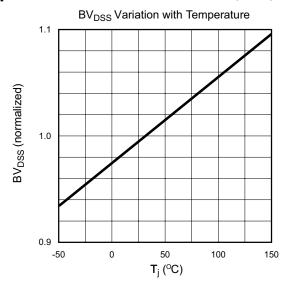


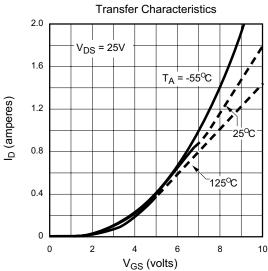


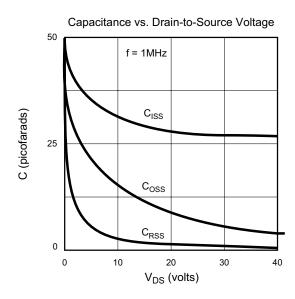


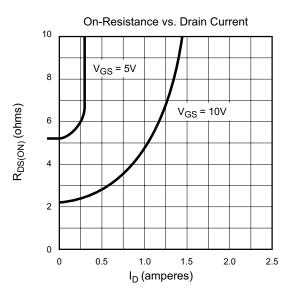


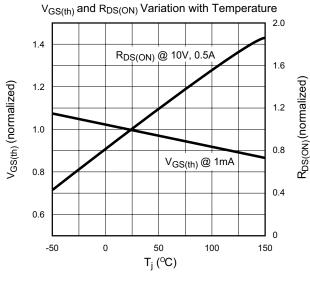
Typical Performance Curves (cont.)

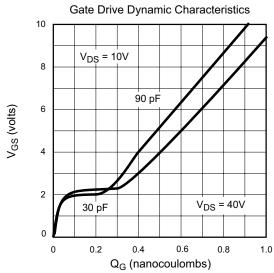






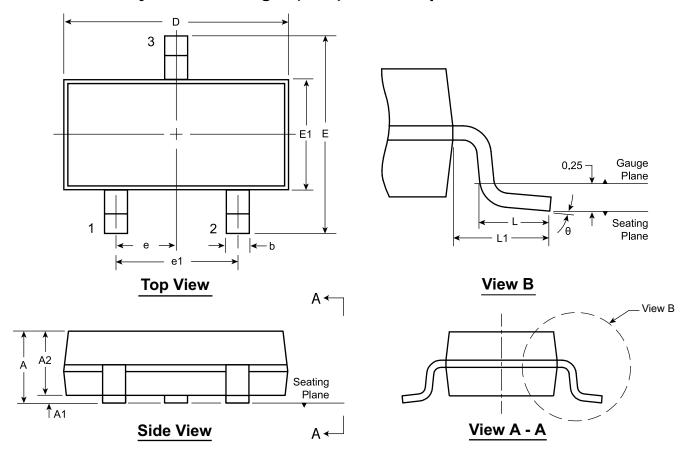






3-Lead TO-236AB (SOT-23) Package Outline (K1)

2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



| Symb | ol | Α | A1 | A2 | b | D | E | E1 | е | e1 | L | L1 | θ |
|----------------|-----|------|------|------|------|------|------|------|-------------|----|----------|-------------|------------|
| Dimension (mm) | MIN | 0.89 | 0.01 | 0.88 | 0.30 | 2.80 | 2.10 | 1.20 | | | 1 11 511 | 0.54 | 0 ° |
| | NOM | - | - | 0.95 | - | 2.90 | - | 1.30 | 0.95 BSC | | | 0.54 REF | - |
| | MAX | 1.12 | 0.10 | 1.02 | 0.50 | 3.04 | 2.64 | 1.40 | | | | IXLI | 8 ° |

JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version B072208.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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[†] This dimension is a non-JEDEC dimension.

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